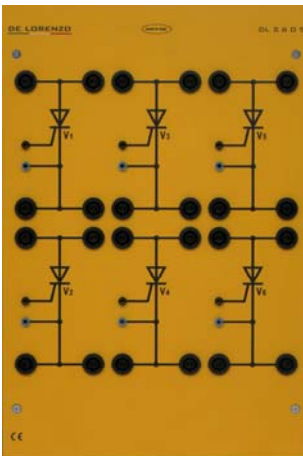




## GROUP OF SCR



DL 2605

Six silicon controlled rectifiers with RCD protection network used for realizing controlled rectifiers and inverters.

### Technical features:

Direct average current:  $I_{TAV} = 7.6 \text{ A max.}$   
True RMS value of the direct current:  $I_{TRMS} = 12 \text{ A}$   
Max. repetitive reverse voltage:  $U_{RRM} = 800 \text{ V}$   
Trigger current:  $I_{GT} = 15 \text{ mA max.}$   
Trigger voltage:  $U_{GT} = 1.5 \text{ V max.}$   
 $I^2t = 72 \text{ A}^2\text{s}$

## TRIAC



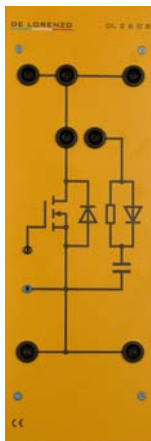
DL 2607

Bidirectional thyristor used for the control in alternated current. Complete with RC suppressor network.

### Technical features:

True RMS value of the direct current:  $I_{TAV} = 8 \text{ A max.}$   
Non-repetitive peak current:  $I_{TSM} = 70 \text{ A, 50Hz (77A, 60Hz)}$   
Max. repetitive reverse voltage:  $U_{DRM} = 800 \text{ V}$   
Trigger current:  $I_{GT} = 25 \text{ mA max. (all the quadrants)}$   
Trigger voltage:  $U_{GT} = 2.5 \text{ V max.}$   
State keeping current:  $I_H = 25 \text{ mA max.}$   
 $I^2t = 24 \text{ A}^2\text{s}$

## MOSFET



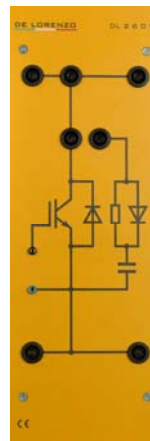
DL 2608

N-channel enhancement mode power MOS with integrated reverse diode (FRED, Fast Recovery Epitaxial Diode) used as very fast switch in switching regulators and inverters.

### Technical features:

Drain-source voltage:  $U_{DS} = 400 \text{ V}$   
Continuous drain current:  $I_D = 10 \text{ A}$   
Drain-source on-state resistance:  $R_{DS(on)} = 0.55 \Omega$   
Gate-source voltage:  $U_{GS} = \pm 20 \text{ V}$

## IGBT



DL 2609

N-channel Insulated Gate Bipolar Transistor (IGBT) with anti parallel hyper fast protection diode used as very fast switch in switching regulators and inverters.

### Technical features:

Collector-emitter voltage:  $U_{CES} = 600 \text{ V}$   
Continuous collector current:  $I_C = 24 \text{ A at } T_C = 25^\circ\text{C}$   
Collector-emitter saturation voltage:  $U_{CESat} = 1.8 \text{ V}_{typ} \text{ at } I_C = 15 \text{ A}$   
Gate-emitter voltage:  $U_{GE} = \pm 20 \text{ V}$